


Description

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

Features

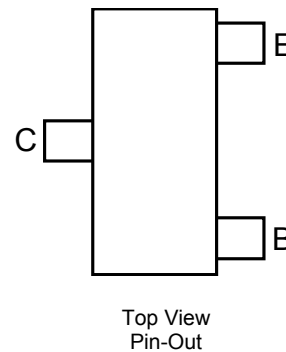
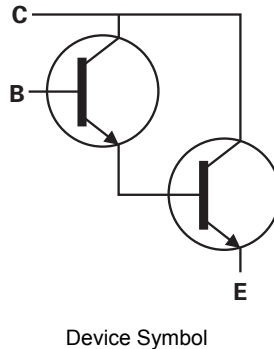
- $BV_{CEO} > 100V$
- $I_C = 900mA$ high Continuous Collector Current
- $I_{CM} = 5A$ Peak Pulse Current
- 625mW Power dissipation
- $h_{FE} > 5k$ up to 2A for high current gain hold up
- Complementary PNP Type: FMMT734Q
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight 0.008 grams (approximate)

Applications

- Automotive
- Lamp
- Relay
- Solenoid Driving

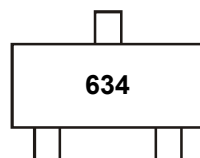


Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT634QTA	Automotive	634	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



634 = Product Type Marking Code

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	120	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	12	V
Continuous Collector Current	I _C	900	mA
Peak Pulse Current	I _{CM}	5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

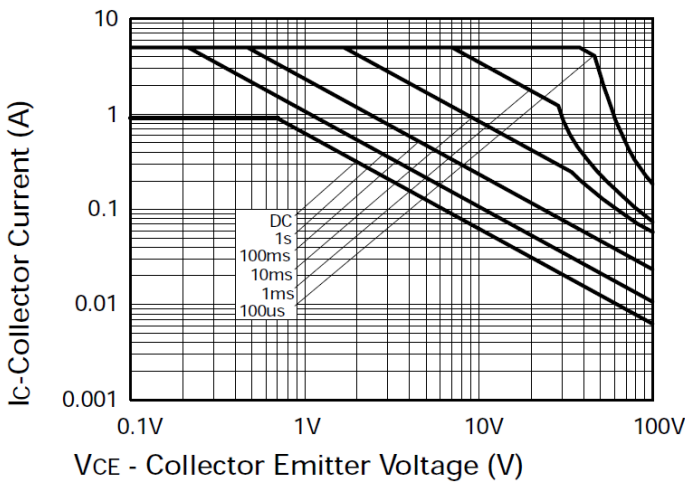
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	625	mW
Power Dissipation (Note 7)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{θJL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

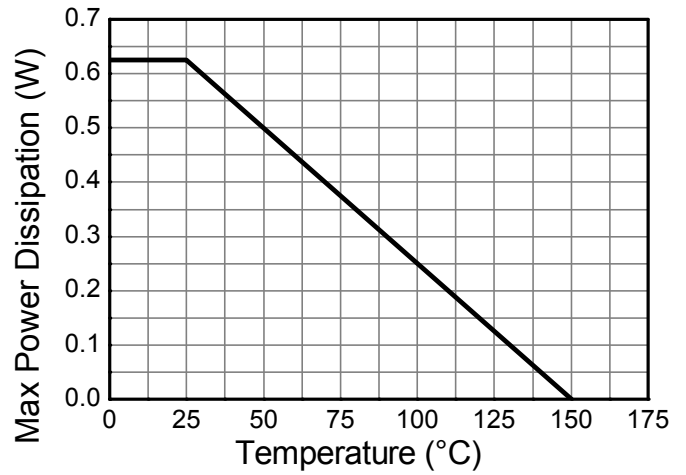
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
6. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as note (6), except the device is measured at t ≤ 5 sec.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

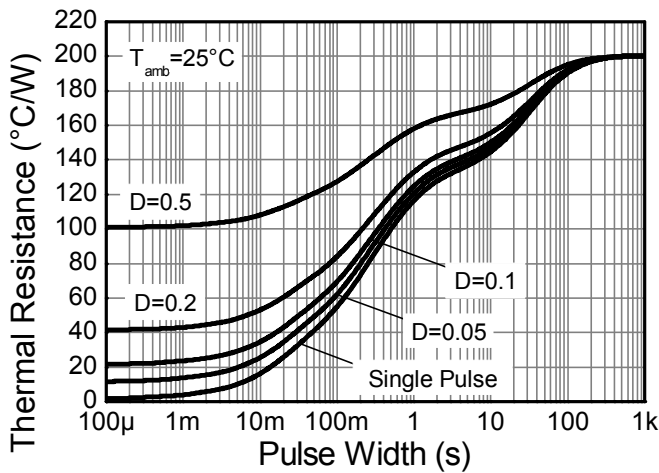
Thermal Characteristics and Derating information



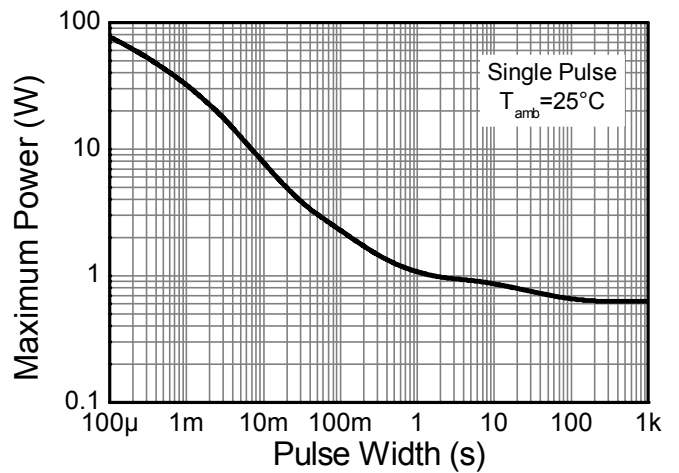
Safe Operating Area



Derating Curve



Transient Thermal Impedance



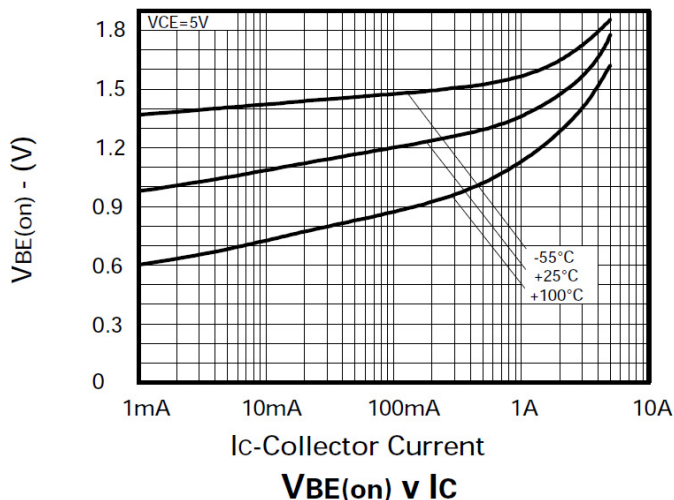
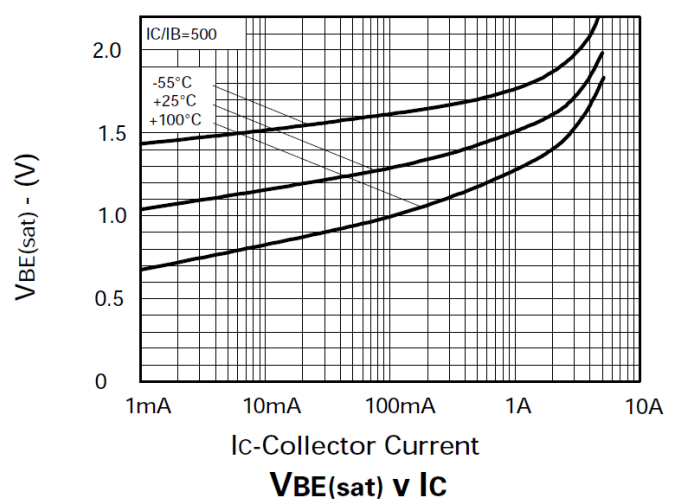
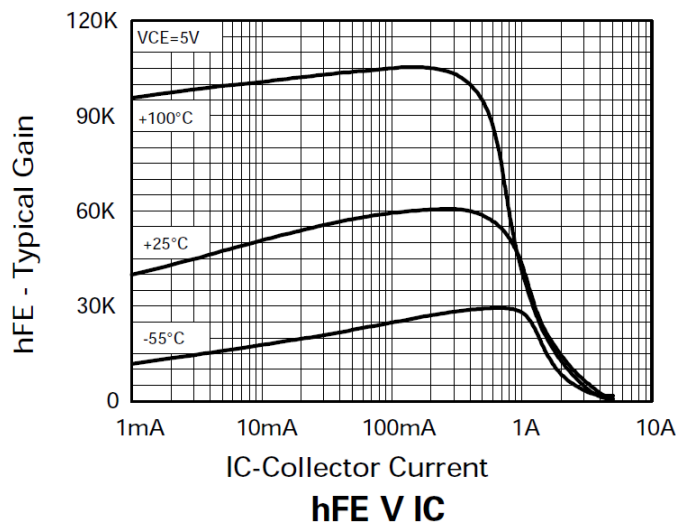
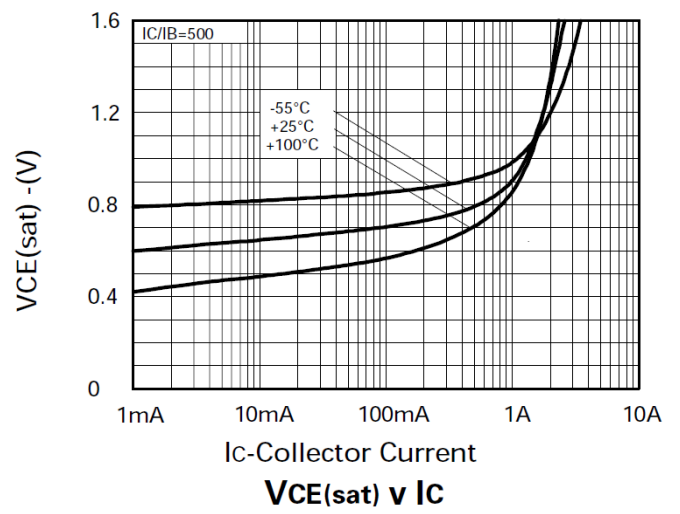
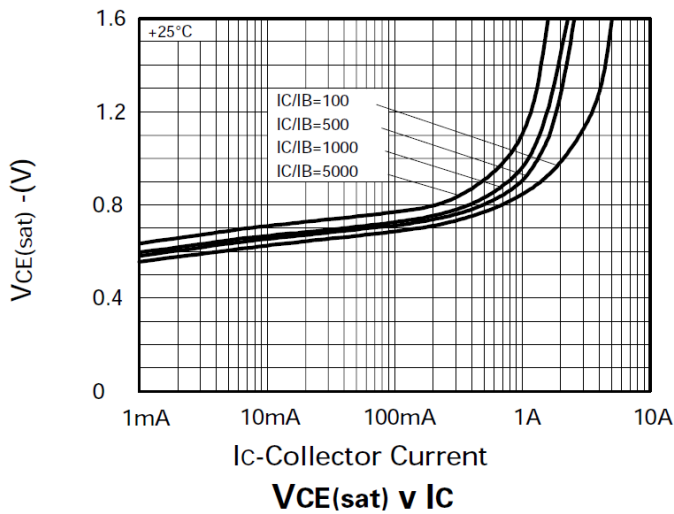
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	120	170	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	100	115	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	12	16	-	V	I _E = 100μA
Collector Cut-off Current	I _{CBO}	-	<1	10	nA	V _{CB} = 80V
Emitter Cut-off Current	I _{EBO}	-	<1	10	nA	V _{EB} = 7V
Collector Emitter Cut-off Current	I _{CES}	-	<1	100	nA	V _{CES} = 80V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	- 20k 15k 5k -	50k 60k 40k 14k 24k 600	- - - - - -	-	I _C = 10mA, V _{CE} = 5V I _C = 100mA, V _{CE} = 5V I _C = 1A, V _{CE} = 5V I _C = 2A, V _{CE} = 5V I _C = 1A, V _{CE} = 2V I _C = 5A, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	- - - - -	0.67 0.72 0.75 0.82 0.68 0.85	0.75 0.80 0.85 0.93 -	V	I _C = 100mA, I _B = 1mA I _C = 250mA, I _B = 1mA I _C = 500mA, I _B = 5mA I _C = 900mA, I _B = 5mA I _C = 900mA, I _B = 5mA, T _J = +150°C I _C = 1A, I _B = 5mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	1.5	1.65	V	I _C = 1A, I _B = 5mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	1.33	1.50	V	I _C = 1A, V _{CE} = 5V
Transition Frequency	f _T	-	140	-	MHz	I _C = 50mA, V _{CE} = 10V, f = 100MHz
Output Capacitance	C _{obo}	-	9	20	pF	V _{CB} = 10V, f = 1MHz
Turn-On Time	t _(on)	-	290	-	ns	V _{CC} = 20V, I _C = 500mA,
Turn-Off Time	t _(off)	-	2,400	-	ns	I _{B1} = -I _{B2} = 1mA

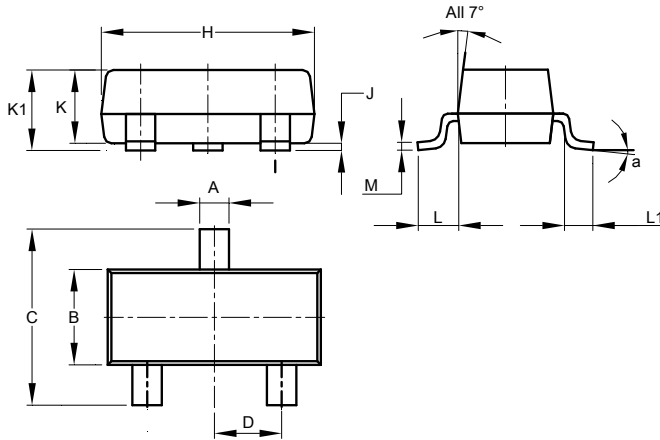
Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

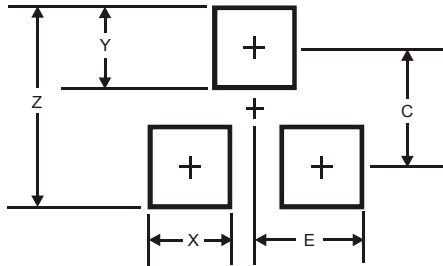
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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